MOSFETs Silicon N-channel MOS (U-MOSⅧ-H)

TK100E08N1

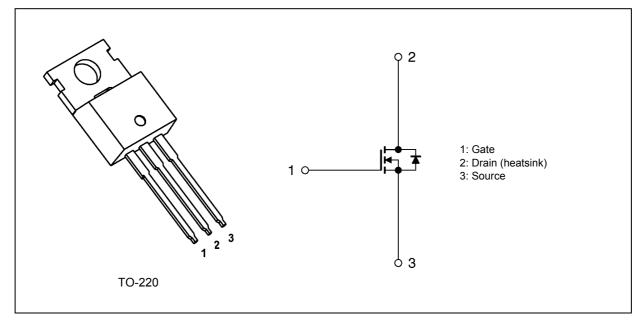
1. Applications

Switching Voltage Regulators

2. Features

- (1) Low drain-source on-resistance: $R_{DS(ON)} = 2.6 \text{ m}\Omega \text{ (typ.)} (V_{GS} = 10 \text{ V})$
- (2) Low leakage current: $I_{DSS} = 10 \ \mu A \ (max) \ (V_{DS} = 80 \ V)$
- (3) Enhancement mode: V_{th} = 2.0 to 4.0 V (V_{DS} = 10 V, I_{D} = 1.0 mA)

3. Packaging and Internal Circuit



4. Absolute Maximum Ratings (Note) ($T_a = 25^{\circ}C$ unless otherwise specified)

Characteristics				Rating	Unit
Drain-source voltage			V _{DSS}	80	V
Gate-source voltage			V _{GSS}	±20	
Drain current (DC)	(Silicon limit)	(Note 1,2)	Ι _D	214	A
Drain current (DC)		(Note 1,3)	Ι _D	100	
Drain current (pulsed)	(t = 1 ms)	(Note 1)	I _{DP}	568	
Power dissipation	(T _c = 25°C)		PD	255	W
Single-pulse avalanche energy		(Note 4)	E _{AS}	278	mJ
Avalanche current			I _{AR}	100	A
Channel temperature			T _{ch}	150	°C
Storage temperature			T _{stg}	-55 to 150	

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Start of commercial production

5. Thermal Characteristics

Characteristics	Symbol	Max	Unit
Channel-to-case thermal resistance	R _{th(ch-c)}	0.49	°C/W
Channel-to-ambient thermal resistance	R _{th(ch-a)}	83.3	

Note 1: Ensure that the channel temperature does not exceed 150°C.

Note 2: Limited by silicon chip capability. Package limit is 100 A.

Note 3: Device mounted with heatsink so that $R_{th(ch-a)}$ becomes 2.77°C/W.

Note 4: V_DD = 64 V, T_ch = 25°C (initial), L = 21.4 μ H,I_{AR} = 100 A

Note: This transistor is sensitive to electrostatic discharge and should be handled with care.

6. Electrical Characteristics

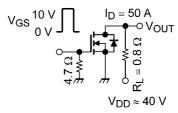
6.1. Static Characteristics (T_a = 25°C unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage current	I _{GSS}	V_{GS} = ±20 V, V_{DS} = 0 V	_	_	±0.1	μA
Drain cut-off current	I _{DSS}	V _{DS} = 80 V, V _{GS} = 0 V	-	—	10	
Drain-source breakdown voltage	V _{(BR)DSS}	I _D = 10 mA, V _{GS} = 0 V	80	_	—	V
Drain-source breakdown voltage (Note 5)	V _{(BR)DSX}	I _D = 10 mA, V _{GS} = -20 V	60	_	_	
Gate threshold voltage	V _{th}	V _{DS} = 10 V, I _D = 1.0 mA	2.0	—	4.0	
Drain-source on-resistance	R _{DS(ON)}	V _{GS} = 10 V, I _D = 50 A	_	2.6	3.2	mΩ

Note 5: If a reverse bias is applied between gate and source, this device enters V_{(BR)DSX} mode. Note that the drainsource breakdown voltage is lowered in this mode.

6.2. Dynamic Characteristics ($T_a = 25^{\circ}C$ unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Input capacitance	C _{iss}	V _{DS} = 40 V, V _{GS} = 0 V, f = 1 MHz	_	9000	_	pF
Reverse transfer capacitance	C _{rss}		_	52	—	
Output capacitance	C _{oss}		_	2100	_	
Gate resistance	r _g	_	_	3.2	_	Ω
Switching time (rise time)	tr	See Figure 6.2.1	_	26	—	ns
Switching time (turn-on time)	t _{on}		_	53	_	
Switching time (fall time)	t _f			46		
Switching time (turn-off time)	t _{off}			140	_	



Duty \leq 1%, t_w = 10 μ s

Fig. 6.2.1 Switching Time Test Circuit

6.3. Gate Charge Characteristics ($T_a = 25^{\circ}C$ unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Total gate charge (gate-source plus gate-drain)	Qg	$V_{DD} \approx 64$ V, V_{GS} = 10 V, I_D = 100 A	_	130	_	nC
Gate-source charge 1	Q _{gs1}		_	45	_	
Gate-drain charge	Q _{gd}]	—	33	_	
Gate switch charge	Q _{SW}]	_	53		

6.4. Source-Drain Characteristics ($T_a = 25^{\circ}C$ unless otherwise specified)

Characteristics		Symbol	Test Condition	Min	Тур.	Max	Unit
Reverse drain current (DC)	(Note 6)	I _{DR}	—	_	_	100	А
Reverse drain current (pulsed)	(Note 6)	I _{DRP}	—	_	—	568	
Diode forward voltage		V _{DSF}	I _{DR} = 100 A, V _{GS} = 0 V	_	—	-1.2	V
Reverse recovery time	(Note 7)	t _{rr}	I _{DR} = 100 A, V _{GS} = 0 V	_	93	_	ns
Reverse recovery charge	(Note 7)	Q _{rr}	-dI _{DR} /dt = 100 A/μs		190	_	nC

Note 6: Ensure that the channel temperature does not exceed 150°C. Note 7: Ensure that V_{DS} peak does not exceed V_{DSS} .

7. Marking

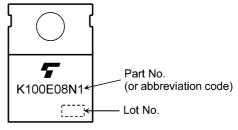
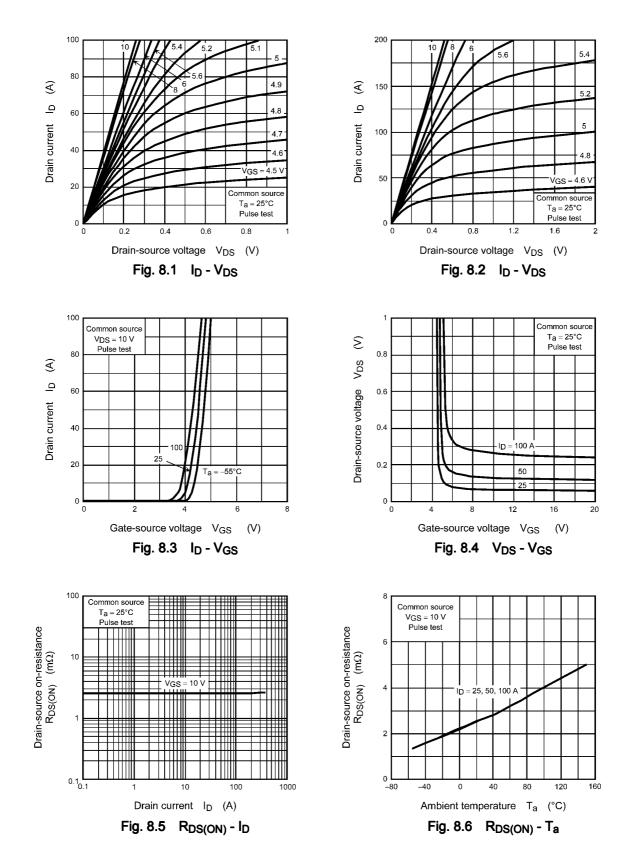


Fig. 7.1 Marking

8. Characteristics Curves (Note)



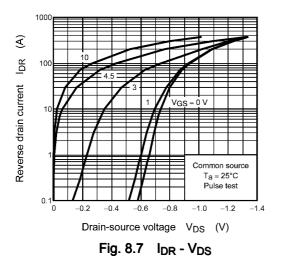
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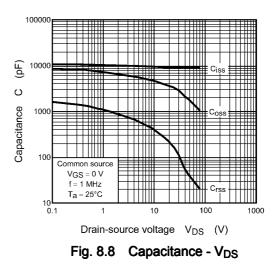
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Common source

VDS = 10 V ID = 1.0 mA

Pulse test



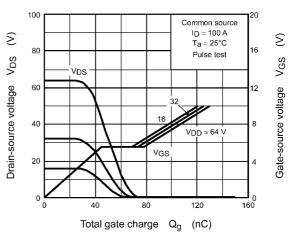
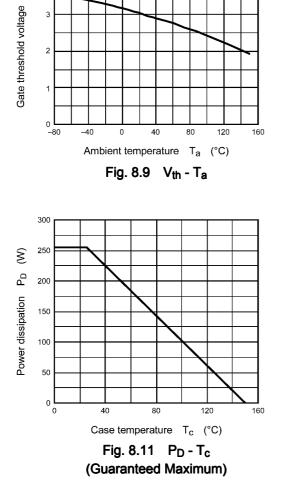


Fig. 8.10 Dynamic Input/Output Characteristics



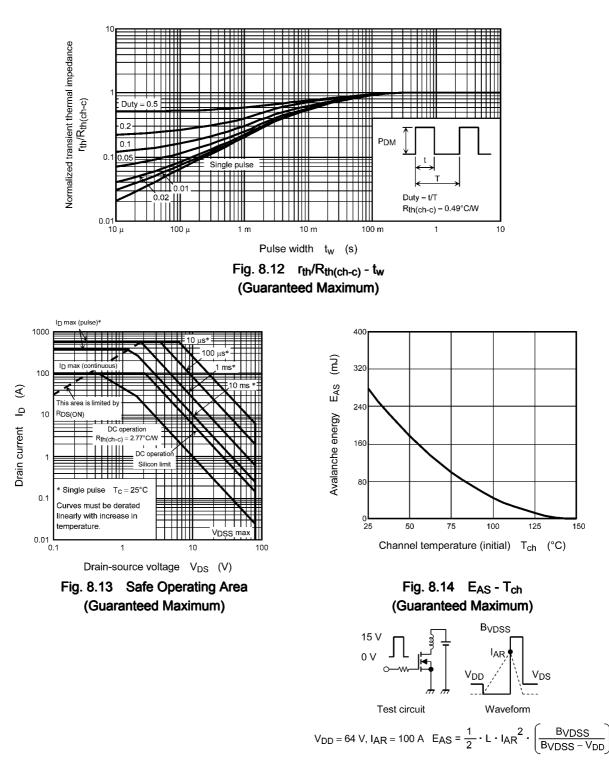
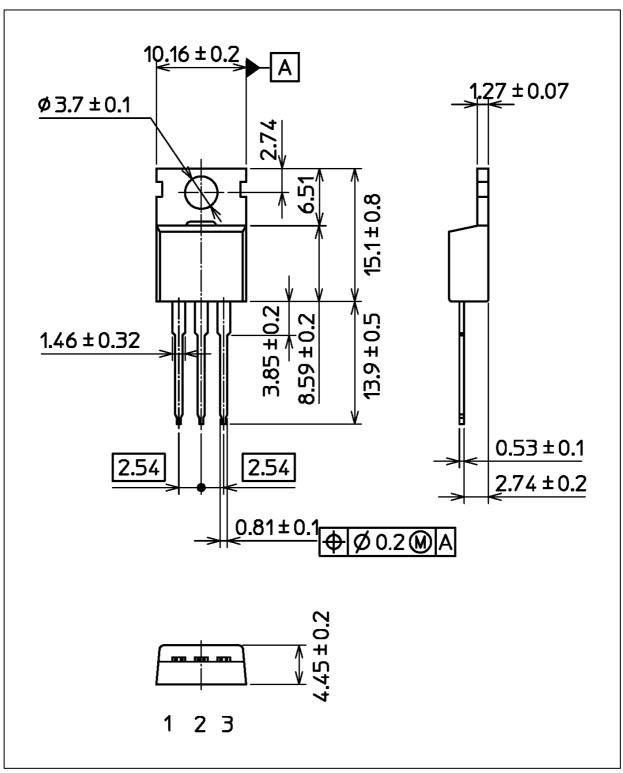


Fig. 8.15 Test Circuit/Waveform

Note: The above characteristics curves are presented for reference only and not guaranteed by production test, unless otherwise noted.







Weight: 1.93 g (typ.)

	Package Name(s)
TOSHIBA: 2-10X1A	
Nickname: TO-220	

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